



IDS #0705

Sheet 1 of 1

Form PTO-1449 (REV. 8-83) <span style="float: right;">US Dept. of Commerce</span> PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			ATTY DOCKET NO. 119232		APPLICATION NO. 10/807,235		
			APPLICANT(S) Akira SAKAI et al.				
			FILING DATE March 24, 2004		GROUP 2826		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS
<i>EP</i>	1	JP 2002-289843 (w/English abstract & machine translation)	10/4/2002	JAPAN		—	—
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
EXAMINER <i>Eva Per+</i>			DATE CONSIDERED <i>11/7/05</i>				
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: July 7, 2005



TPS #1005

Sheet 1 of 1

Form PTO-144 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE			ATTY DOCKET NO. 119232		APPLICATION NO. 10/807,235		
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			APPLICANT(S) Akira SAKAI et al.				
			FILING DATE March 24, 2004		GROUP 2826		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS
EP	1.	6,509,283	01-21-2003	Thomas		—	—
EP	2.	2003/0020068 A1	01-30-2003	Finder		—	—
EP	3.	2002/0197793 A1	12-26-2002	Dornfest et al.		—	—
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
EP	4.	European Search Report dated September 19, 2005					
EP	5.	Osten, et al., <u>Epitaxial Praseodymium Oxide: A new high-K dielectric</u> , pp. 100-106, JWGI (2001)					
EP	6.	<u>Liu, et al., Epitaxial growth of Pr<sub>2</sub>O<sub>3</sub> on Si(111) and the observation of a hexagonal to cubic phase transition during postgrowth N<sub>2</sub> annealing</u> , 79(5):671-673, Applied Physics Letters (July 30, 2001)					
EP	7.	<u>Ferrari, et al., Chlorine mobility during annealing in N<sub>2</sub> in ZrO<sub>2</sub> and HfO<sub>2</sub> films grown by atomic layer deposition</u> , 92(12):7675-7677, J. of Applied Physics (December 15, 2002)					
EP	8.	<u>Murawala, et al., Plasma Enhanced Liquid Source-CVD and Rapid Thermal Annealing of Tantalum Penta Oxide Dielectric Material</u> , Materials, Tsukuba, pp. 527-529 (1992)					
EP	9.	<u>Mereu, et al., Fowler-Nordheim Tunneling in Epitaxial Yttrium Oxide on Silicon for High-K Gate Applications</u> , Proceedings of the IEEE International Semiconductor Conference, 2:309-312 (October 8, 2002)					
<b>EXAMINER</b> <i>Evan Pert</i>			<b>DATE CONSIDERED</b> <i>11/3/05</i>				
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: October 31, 2005